

**Table 10 Monolithic Integrated Circuit Screening Requirements**

Inspection/ Test	Methods	MIL-STD-883 Conditions and Requirements	Grade 1	Grade 2
1. Wafer Acceptance	5007		X	
2. Nondestructive Bond Pull	2023		X	
3. Internal Visual	2010	Condition A or B (Note 1).	X	X
4. Temperature Cycling	1010	Condition C (-65 °C to + 150 °C) in N <sub>2</sub> atmosphere. 20 cycles.	X	X
5. Constant Acceleration	2001	Condition E (Note 2). Y <sub>1</sub> orientation only.	X	X
6. PIND	2020	Condition A.	X	X
7. Radiographic	2012	1 view for Quad Flat Pack and Leadless Chip Carrier. 2 views for other package styles. Can be performed at any time after PIND.	X	
8. Serialization			X	
9. Initial Electrical Measurements		Read and record delta parameters per Table 10A.	X	X
10. Burn-In (Note 3)	1015	Condition C and/or D per Table 10A. Duration (hours) for Static/Dynamic burn-in as required in Table 10A.	X 72/240	X 160
11. Final Electrical Measurements		Per Table 10A.	X	X
12. Calculate Deltas		See Table 10A.	X	
13. Percent Defective Allowable		PDA applies to delta, selected DC and functional tests at test temperature of 25 °C.	$\Delta$ +DC $\leq$ 5% Functional $\leq$ 3%	DC $\leq$ 10%
14. Hermetic Seal a. Fine Leak b. Gross Leak	1014	Condition A or B. Condition C.	X	X
15. External Visual	2009	3 X to 10X.	X	X

**Notes:**

1. Destructive Physical Analysis may be performed to the requirements of S311-M-70 in lieu of internal visual for devices used in Grades 2 applications.
2. For packages having a cavity perimeter of 2 inches or more in total length, or having a mass greater than 5 grams, test condition D can be used.
3. A dynamic burn-in or a static burn-in shall be performed in accordance with Table 10A. Static and dynamic burn-in is required for Grade 1 parts when so indicated in Table 10A. A dynamic or static burn-in shall be performed in accordance with Table 10A for Grade 2 parts.

**Table 10A Burn-In and Electrical Measurement Requirements for Monolithic ICs (Page 1 of 4)**

IC Type	Required Burn-In (Note 4)		Delta	Electrical Measurements (Notes 1, 2, 3)
	Static (Condition C)	Dynamic (Condition D)		
<b>Digital Bipolar &amp; Digital MOS/ BiCMOS:</b> (Note 6) LOGIC (Gates, Buffers, Flip-Flops, Multiplexers, Registers and Counters) RAMs FIFOs Microprocessors Interface Peripherals ASICs FPGA, PROM, PLA (Note 5)	Not required for Digital Bipolar Technology.  Required for Digital MOS Technology.  $T_A \geq 125\text{ }^{\circ}\text{C}$  $V_{in} = V_{DD}$ across one-half input pins and $V_{SS}$ across the remaining inputs.  $V_{out} = 0.5 V_{DD}$ through $R_L$	Required for both technologies.  $T_A \geq 125\text{ }^{\circ}\text{C}$  $V_{in}$ = Square wave, 50% Duty Cycle to input pins and control pins.  Frequency= 100 Hz to 1 Mhz.  $V_{out} = V_{CC} / 2$ or $V_{DD} / 2$ through $R_L$ .	$\Delta I_{CC}$ or $\Delta I_{DD}$	<b>DC:</b> $V_{IC}$ , $V_{OH}$ , $V_{OL}$ , $I_{CC}(I_{EE})$ , $I_{IL}$ , $I_{IH}$ , $I_{DD}$ , $I_{OZL}$ , $I_{OZH}$ , $I_{OS}$  <b>AC:</b> $T_{PLH}$ , $T_{PHL}$ , $T_{TLH}$ , $T_{THL}$ , $T_{PZH}$ , $T_{PHZ}$ , $T_{PLZ}$ , $T_{PZL}$ , $T_A$ , $T_S$ , $T_H$  <b>Functional Tests:</b> a) for simple logic devices, verify truth table  b) for complex logic devices such as ASIC, FPGA, microprocessors, functional testing includes fault coverage calculations required per Mil-Std-883, Method 5012.  c) for PROMs, check fuse map; for RAMs, perform pattern sensitive tests such as March, galpat, etc.
<b>Linear MOS, Bipolar, and Bi-FET:</b> (Note 7) Op-Amp, Instrument Amplifiers, S/H, and Comparator	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{out}$ = Terminated to ground through $R_L$	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{in}$ = Square wave or sinewave $F = 10\text{ Hz to } 100\text{ KHz}$ , 50% duty cycle $V_{out}$ = Terminated to ground through $R_L$	$\Delta I_{IB}$ $\Delta I_{IO}$ $\Delta V_{IO}$	<b>DC:</b> $I_{CC}$ , $I_{EE}$ , $I_{IO}$ , $V_{IO}$ , $V_{OPP}$ , $A_V$ , CMRR, PSRR  <b>AC:</b> Slew rate

See notes on page C-35.

**Table 10A Burn-In and Electrical Measurement Requirements for Monolithic ICs (Page 2 of 4)**

IC Type	Required Burn-In (Note 4)		Delta	Electrical Measurement (Notes 1, 2, 3)
	Static (Condition C)	Dynamic (Condition D)		
<b>Linear MOS, Bipolar and JFET:</b> (Note 7) Line Drivers and Receivers	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{in} = V_{DD}$ max across one-half input pins and $V_{SS}$ across the remaining inputs.	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{in}$ = Square wave at a specified Vdc  $V_{out} = V_{CC}$ through $R_L$	$\Delta I_{CC}$ $\Delta I_{IH}$	<b>DC:</b> $V_{OH}$ , $V_{OL}$ , $I_{CC}$ , $I_{IL}$ , $I_{IH}$ , $I_{OS}$  <b>AC:</b> $T_{PLH}$ , $T_{PHL}$ , $T_{TLH}$ , $T_{THL}$  <b>Functional Test:</b> verify truth table
<b>Linear MOS, Bi-FET, and Bipolar:</b> (Note 6) Analog Switches and Multiplexers	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{in} = V_{DD}$ max across one-half of inputs and $V_{SS}$ across the other remaining inputs. $V_{out} = \pm V_{CC}$ through $R_L$	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{in}$ = Square wave $F = 100\text{ KHz}$ and 50% duty cycle $V_{out} = \pm V_{CC}$ through $R_L$	$I_{CC}$ $I_{D(OFF)}$ $I_{S(OFF)}$ $R_{(ON)}$	<b>DC:</b> $I_{CC}$ , $I_{D(ON)}$ , $R_{(ON)}$ , $I_{D(OFF)}$ , $I_{S(ON)}$ , $I_{S(OFF)}$  <b>AC:</b> $T_{(ON)}$ , $T_{(OFF)}$ break- before- make- time
<b>Linear Bipolar:</b> Voltage Regulators	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{out}$ = Terminated to ground through $R_L$	Not required	$\Delta I_{SCD}$ $\Delta V_{OUT}$	<b>DC:</b> $I_{CC}$ , $V_{OUT}$ , $I_{OS}$ , line/load regulation
<b>Linear Bipolar:</b> Pulse-width-modulator	Not required	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{out}$ = Terminated to ground through $R_L$ $R_{ext}$ , $C_{ext}$ connected if applicable.	$\Delta I_{IO}$ $\Delta V_{REF}$	<b>DC:</b> $V_{REF}$ , $I_{IB}$ , $I_{IO}$ , $I_{OS}$ , $V_{IO}$ , $V_{OL}$ , $V_{OH}$ , $A_V$ , $CMRR$ , $PSRR$  <b>AC:</b> $T_R$ , $T_F$ , $f_{OSC}$
<b>Darlington Transistor Array</b>	$T_A \geq 125\text{ }^{\circ}\text{C}$ $V_{out} = 15\text{ Vdc}$ through $R_L$	Not required	$\Delta I_{CEX}$ $\Delta h_{FE}$	<b>DC:</b> $V_{CE(SAT)}$ , $V_F$ , $I_{CEX}$ , $I_F$ <b>AC:</b> $h_{FE}$ , $t_{PHL}$ , $t_{PLH}$
<b>Linear CMOS</b> Timers	$T_A \geq 125\text{ }^{\circ}\text{C}$  $V_{out} = V_{CC}$ through $R_L$	Not required	$\Delta I_{CEX}$ $\Delta V_{OH}$ $\Delta V_{OL}$	<b>DC:</b> $V_{TRIG}$ , $V_{TH}$ , $V_R$ , $V_{OL}$ , $V_{OH}$ , $V_{SAT}$ , $I_{CC}$ , $I_{TRIG}$ , $I_{TH}$ , $I_R$ , $I_{CEX}$  <b>AC:</b> $T_{TLH}$ , $T_{THL}$

See notes on page C-35.

**Table 10A Burn-In and Electrical Measurement Requirements for Monolithic ICs (Page 3 of 4)**

IC Type	Required Burn-In (Note 4)		Delta	Electrical Measurement (Notes 1, 2, 3)
	Static (Condition C)	Dynamic (Condition D)		
<b>Linear MOS and Bipolar:</b> Active Filters	Not required	$T_A \geq 125^\circ\text{C}$ $V_{in}$ = Sine wave at Frequency $< f_O$ $V_{out}$ = Terminated to ground through $R_L$	$\Delta I_{CC}$ $\Delta V_{OS}$	<b>DC:</b> $I_{CC}$ , $I_{SS}$ , $V_{OS}$  <b>AC:</b> $f_O$ , Q, input frequency range
<b>Mixed Signal MOS, Bi-CMOS and Bipolar:</b> (Note 7) Analog to Digital (A/D) Converters.	$T_A \geq 125^\circ\text{C}$ $V_{in}$ = Max analog dc input $V_{out} = V_{CC}/2$ through $R_L$	$T_A \geq 125^\circ\text{C}$ $V_{in}$ = Analog input to generate maximum digital codes.  $V_{out} = V_{CC}/2$ through $R_L$	$\Delta I_{CC}$ $\Delta I_{EE}$ $\Delta V_{IO}$	<b>DC:</b> $V_{REF}$ , $V_{OH}$ , $V_{OL}$ , $V_{IO}$ , $I_{CC}$ , $I_{EE}$ , $I_{IL}$ , $I_{IH}$ , $I_{OZL}$ , $I_{OZH}$ , $I_{OS}$ , Zero Error, Gain Error, Linearity Error. <b>AC:</b> $T_C$ , $T_S$ , $T_H$ <b>Functional Test:</b> Verify codes
<b>Mixed Signal MOS, Bi-CMOS and Bipolar</b> (Note 7) Digital to Analog (D/A) Converters.	$T_A \geq 125^\circ\text{C}$ $V_{in} = V_{DD}$ on one-half data inputs and $V_{SS}$ on remaining inputs. $V_{out}$ = Terminated to ground thru $R_L$	$T_A \geq 125^\circ\text{C}$ $V_{in}$ = Apply appropriate digital codes for all inputs and for control signals.  $V_{out}$ = Terminated to ground through $R_L$ .	$\Delta I_{CC}$ $\Delta I_{EE}$	<b>DC:</b> $I_{CC}$ , $I_{EE}$ , $I_{IL}$ , $I_{IH}$ , $I_{OZL}$ , $I_{OZH}$ , $I_{OS}$ , Zero Error, Gain Error, Linearity Error, PSRR <b>AC:</b> $T_C$ , $T_S$ , $T_H$ <b>Functional Test:</b> Verify codes

**Notes:**

1. See MIL-S-1331 for symbol definitions.
2. These are typically recommended electrical parameters. Since electrical parameters are device dependent, refer to detail specifications for actual DC and AC parametric test conditions and limits.
3. For digital devices, all DC parameters, functional tests, and switching tests shall be tested at  $25^\circ\text{C}$ , at minimum operating temperature and at maximum operating temperature. AC tests (e.g  $C_{IN}$ ) are tested initially and after any design or process changes.  
For linear devices, all DC parameters shall be tested at  $25^\circ\text{C}$ , at minimum operating temperature and at maximum operating temperature. All AC and switching tests shall be performed at  $25^\circ\text{C}$ .
4. Static and Dynamic burn-in shall be performed at maximum recommended operating supply voltage with  $V_{in}$  and  $R_L$  selected to assure that the junction temperature shall not exceed  $T_{jmax}$  specified for the device type.
5. For one-time programmable devices, (e.g. PROMs, PALs and FPGAs) dynamic burn-in shall be performed on programmed devices with user application specific burn-in circuit. The post burn-in should include DC, AC, and functional tests for user's program verification.
6. Dynamic burn-in required for Grade 2 parts.
7. Static or dynamic burn-in acceptable for Grade 2 parts.

**Table 10B    Hybrid Integrated Circuit Screening Requirements**

Inspection/ Test	Methods	MIL-STD-883 Conditions and Requirements	Grade 1	Grade 2
1. Pre-seal Burn-in	1030		Optional	Optional
2. Nondestructive Bond Pull	2023	PDA $\leq$ 2% or 1 wire.	X	
3. Internal Visual	2017	Condition A or B. (Note 1)	X	X
4. Stabilization Bake	1008	Condition C	X	X
4. Temperature Cycling	1010	Condition B (-55 °C to +125 °C) for 10 cycles	X	X
5. Constant Acceleration	2001	Condition A Y <sub>1</sub> orientation only	X	X
6. PIND	2020	Condition A or B.	X	X
7. Radiographic	2012	Can be performed at any sequence after PIND.	X	
8. Serialization			X	
9. Initial Electrical Measurements		Electrical measurements and delta parameters are done per applicable device specification (Note 2).	X	X
10. Burn-In	1015	Condition A, B, C, or D @ T <sub>A</sub> $\geq$ 100 °C. Duration (hours) for Static /Dynamic burn-in (Note 2, 3).	X 160/160	X 160
11. Final Electrical Measurements		For Grade 1, interim electrical tests shall be performed after the first 160-hour burn-in.	X	X
12. Calculate Deltas		Per applicable device specification	X	
13. Calculate PDA		PDA applies to selected DC tests and delta for Grade 1 during the second burn-in only.	$\Delta$ +DC $\leq$ 2%	DC $\leq$ 10%
14. Hermetic Seal a. Fine Leak b. Gross Leak	1014	Condition A or B Condition C	X	X
15. External Visual	2009	3 X to 10X	X	X

**Notes:**

1. Destructive Physical Analysis may be performed to the requirements of S311-M-70 in lieu of internal visual for devices used in Grades 2.
2. Burn-in and electrical measurements are not included for hybrids due to many customer designs and many different functional configurations; they shall be specified in the detail specifications or altered item drawings.
3. For Grade 1 parts, the burn-in period shall be divided into two successive 160- hour minimum burn-in; included in that total 320-hour time may be a combined static and dynamic configurations. For Grade 2 parts, only one burn-in is required, and it can be either static mode or dynamic mode.